

Dual N-Channel 20-V (D-S) MOSFET

Key Features:

- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed

Typical Applications:

- Power Routing
- Li Ion Battery Packs
- Level Shifting and Driver Circuits

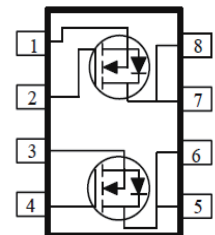
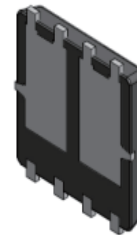
PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ (m Ω)	I_D (A)
20	7 @ $V_{GS} = 4.5V$	50 ^c
	9 @ $V_{GS} = 2.5V$	50 ^c

DFN5X6-8L



RoHS
COMPLIANT
HALOGEN
FREE



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	Limit	Units
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	± 12	
Continuous Drain Current	$T_A = 25^\circ\text{C}$	I_D	16 ^a	A
	$T_A = 70^\circ\text{C}$		13 ^a	
	$T_C = 25^\circ\text{C}$	I_D	50 ^c	
	$T_C = 70^\circ\text{C}$		50 ^c	
Pulsed Drain Current ^b		I_{DM}	80	
Continuous Source Current (Diode Conduction) ^a		I_S	4.3	
Power Dissipation	$T_A = 25^\circ\text{C}$	P_D	2.5 ^a	W
	$T_A = 70^\circ\text{C}$		1.6 ^a	
	$T_C = 25^\circ\text{C}$		36	
	$T_C = 70^\circ\text{C}$		23	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$t \leq 10$ sec	$R_{\theta JA}$	50	$^\circ\text{C/W}$
	Steady State		70	
Maximum Junction-to-Case	Steady State	$R_{\theta JC}$	3.5	

Notes

- Surface Mounted on 1" x 1" FR4 Board
- Pulse width limited by maximum junction temperature
- Package limited

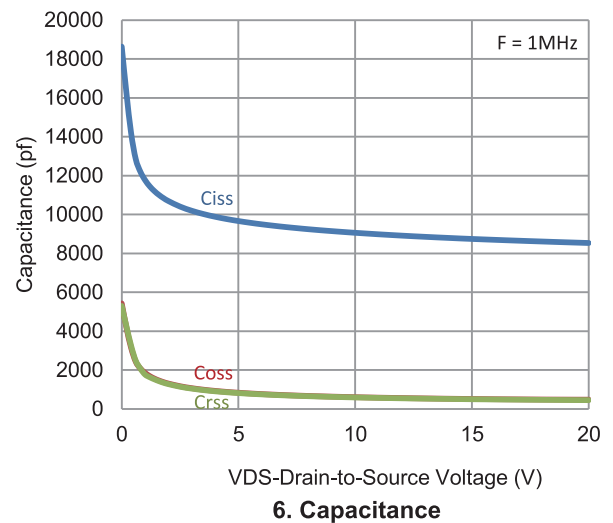
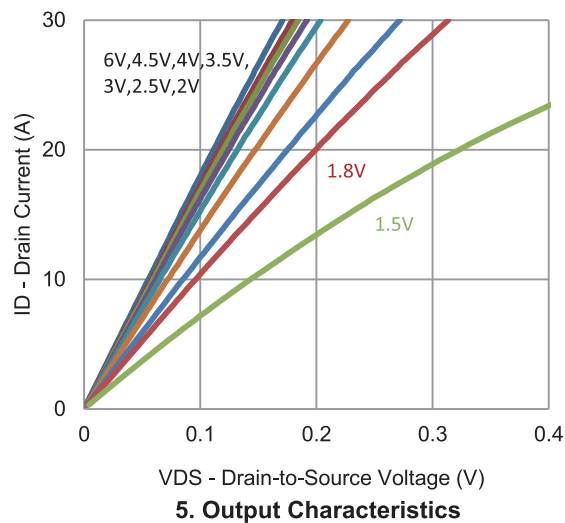
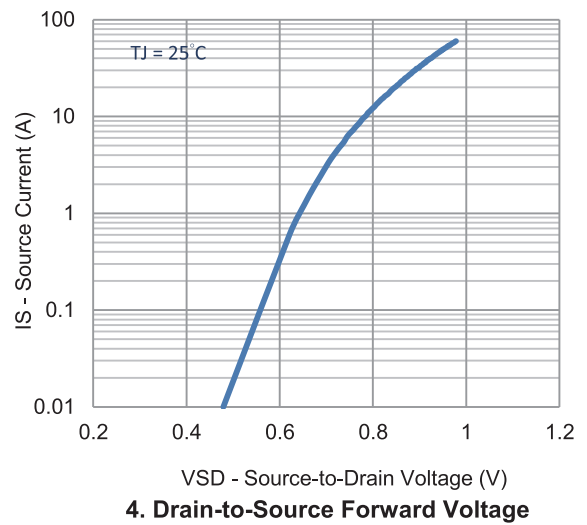
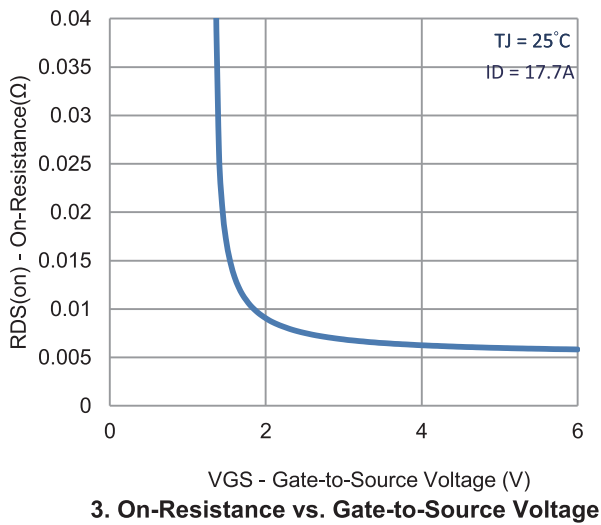
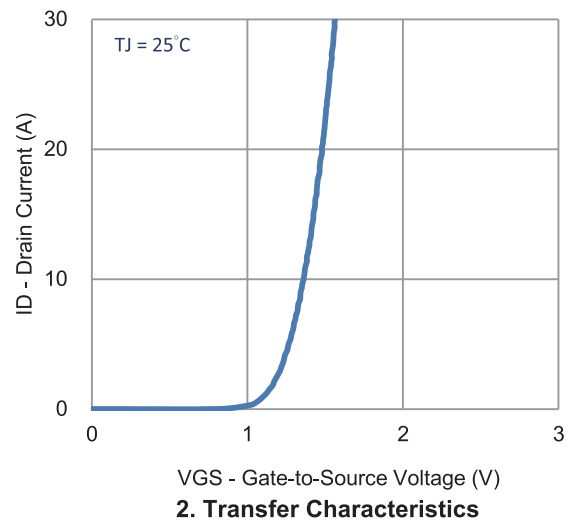
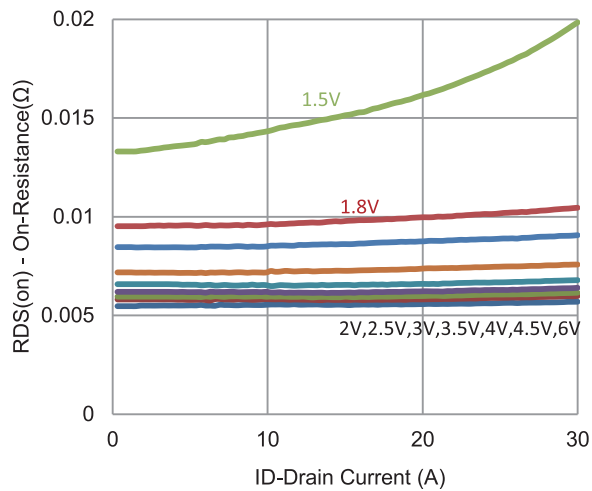
Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.4			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 12 V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16 V, V_{GS} = 0 V$			1	μA
		$V_{DS} = 16 V, V_{GS} = 0 V, T_J = 55^\circ C$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5 V, V_{GS} = 4.5 V$	30			A
Drain-Source On-Resistance ^a	$r_{DS(on)}$	$V_{GS} = 4.5 V, I_D = 17.7 A$			7	m Ω
		$V_{GS} = 2.5 V, I_D = 14.2 A$			9	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15 V, I_D = 17.7 A$		12		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.2 A, V_{GS} = 0 V$		0.68		V
Dynamic ^b						
Total Gate Charge	Q_g	$V_{DS} = 10 V, V_{GS} = 4.5 V,$ $I_D = 17.7 A$		73		nC
Gate-Source Charge	Q_{gs}			7.8		
Gate-Drain Charge	Q_{gd}			17		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = 10 V, R_L = 0.6 \Omega,$ $I_D = 17.7 A,$ $V_{GEN} = 4.5 V, R_{GEN} = 1 \Omega$		16		ns
Rise Time	t_r			36		
Turn-Off Delay Time	$t_{d(off)}$			169		
Fall Time	t_f			36		
Input Capacitance	C_{iss}	$V_{DS} = 15 V, V_{GS} = 0 V, f = 1 Mhz$		8742		pF
Output Capacitance	C_{oss}			511		
Reverse Transfer Capacitance	C_{rss}			498		

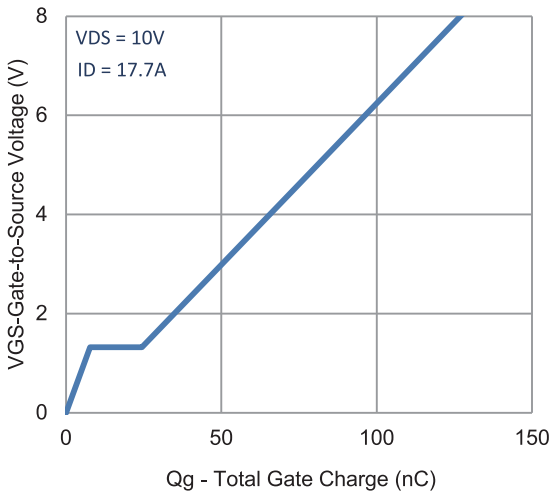
Notes

- a. Pulse test: PW $\leq$ 300us duty cycle $\leq$ 2%.
- b. Guaranteed by design, not subject to production testing.

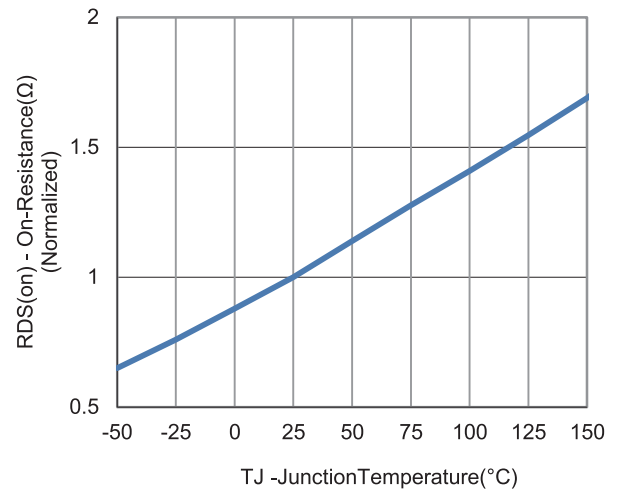
Typical Electrical Characteristics



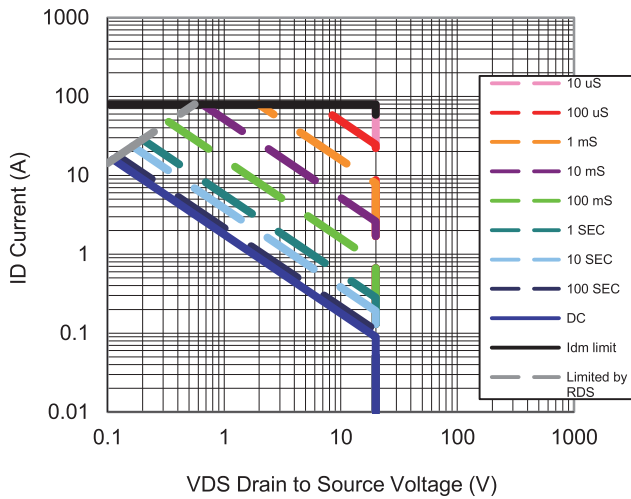
Typical Electrical Characteristics



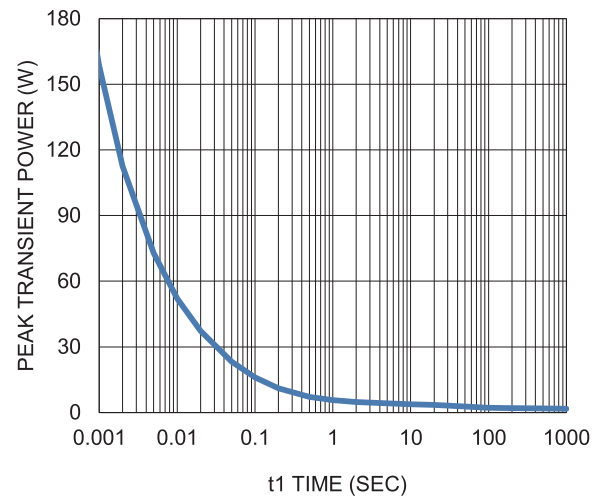
7. Gate Charge



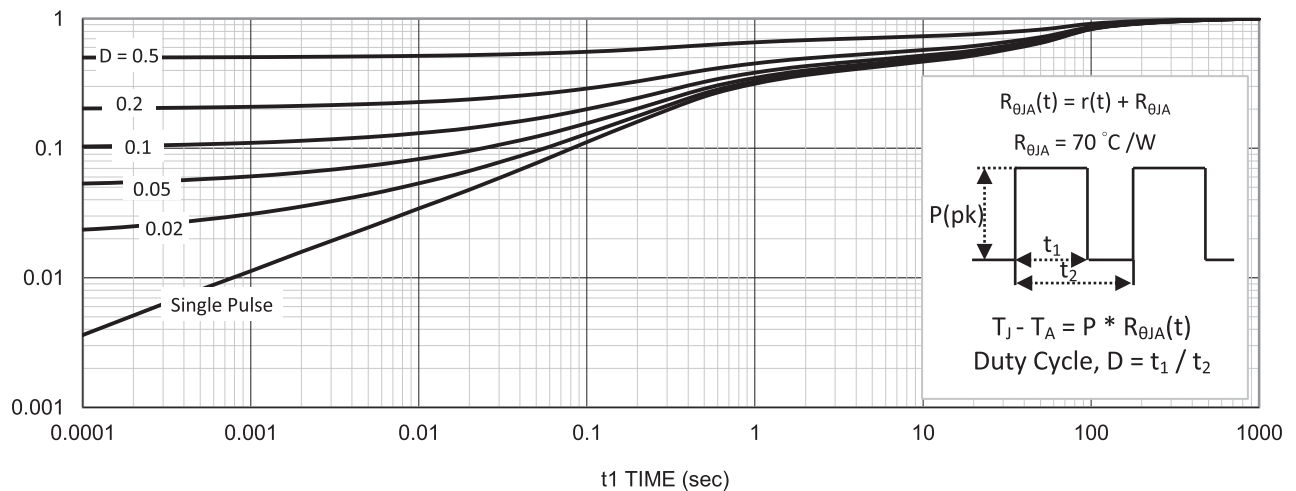
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area

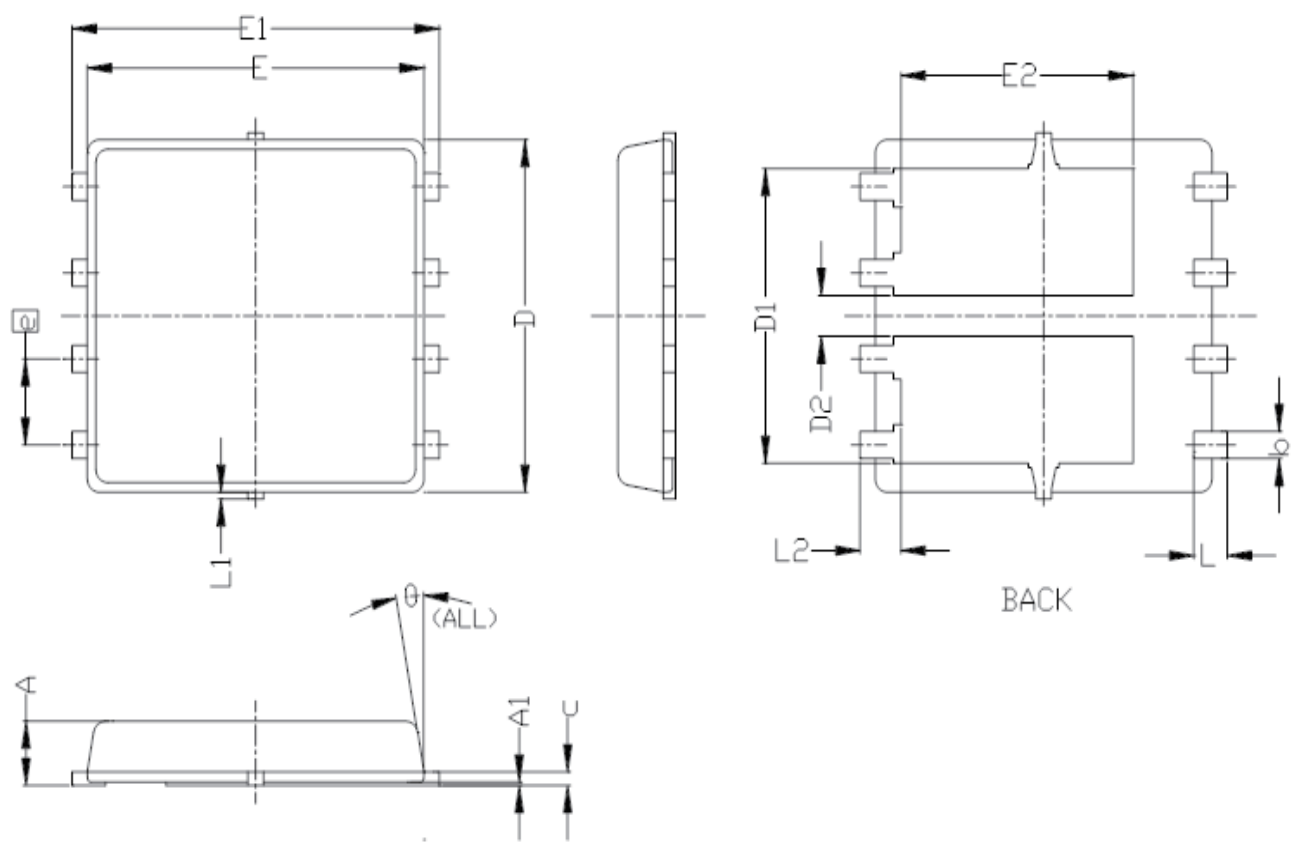


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0.95	1.00	0.033	0.037	0.039
A1	0.00	—	0.05	0.000	—	0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
c	0.15	0.20	0.25	0.006	0.008	0.010
D	5.20 BSC			0.205 BSC		
D1	4.35 BSC			0.171 BSC		
E	5.55 BSC			0.219 BSC		
E1	6.05 BSC			0.238 BSC		
E2	3.62 BSC			0.143 BSC		
e	1.27 BSC			0.050 BSC		
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0	—	0.15	0	—	0.006
L2	0.68 REF			0.027 REF		
θ	0°	—	10°	0°	—	10°